,	IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
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3	Filing Date
4	Assignee         Micron Technology, Inc.           Group Art Unit         2822           Examiner         M. Trinh
5	Attorney's Docket No. MI22-898  Title: Semiconductor Processing Methods of Forming a Conductive Gate and Line
6	THE. Semiconductor 110cosing methods of 1 oraning a conductive Gate and Line
7	SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
8	PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98 FAX COPY RECEIVED
9	JUN 0 8 2000 TECHNOLOGY CENTER 2800
10	In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, the Examiner's attention is
11	directed to the references listed on the attached Form PTO-1449 and copies of which
12	are attached. No admission is made regarding whether all the submitted references are
13	prior art.
14	Citation of these patents is respectfully requested.
15	
16	Respectfully submitted,
17	N. O. Sono
18	Dated: May 9, 7600  By: Bernard Berman
19	Reg. No. 37,279 Wells, St. John, Roberts,
20	Gregory & Matkin, P.S.

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Inventor: Title:

Pai-Hung Pan

Semiconductor Processing Methods of Forming a Conductive Ju

Gate and Line

Assignee:

Micron Technology, Inc.

Serial No.:

09/059,644

Filed:

April 13, 1998

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§ 1.56, 137 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, the Examiner's attention is directed to the references listed on the attached Form PTO-1449 and copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of these patents is respectfully requested.

Respectfully submitted,

Attorney:

Bernard Berman

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